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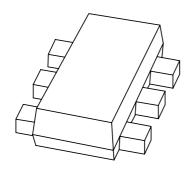
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



PBSS2515VS15 V low V_{CE(sat)} NPN double transistor

Product data sheet Supersedes data of 2001 Nov 07 2004 Dec 23



15 V low V_{CE(sat)} NPN double transistor

PBSS2515VS

FEATURES

- 300 mW total power dissipation
- Very small 1.6 × 1.2 mm ultra thin package
- · Excellent coplanarity due to straight leads
- · Low collector-emitter saturation voltage
- · High current capability
- Improved thermal behaviour due to flat lead
- Replaces two SC-75/SC-89 packaged low V_{CEsat} transistors on same PCB area
- · Reduces required PCB area
- · Reduced pick and place costs.

APPLICATIONS

- · General purpose switching and muting
- Low frequency driver circuits
- LCD backlighting
- · Audio frequency general purpose amplifier applications
- Battery driven equipment (mobile phones, video cameras and hand-held devices).

DESCRIPTION

NPN low V_{CEsat} double transistor in a SOT666 plastic package.

PNP complement: PBSS3515VS.

MARKING

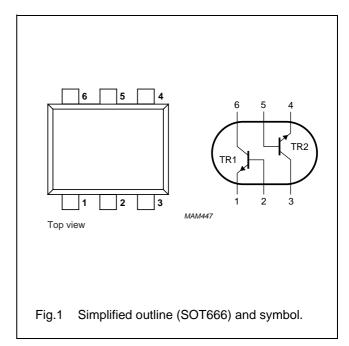
TYPE NUMBER	MARKING CODE
PBSS2515VS	N9

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V _{CEO}	collector-emitter voltage	15	V
I _{CM}	peak collector current	1	Α
R _{CEsat}	equivalent on-resistance	<500	mΩ

PINNING

PIN	DESCRIPTION		
1, 4	emitter	TR1; TR2	
2, 5	base	TR1; TR2	
6, 3	collector	TR1; TR2	



ORDERING INFORMATION

TYPE NUMBER		PACKAGE			
ITPE NOMBER	NAME DESCRIPTION		VERSION		
PBSS2515VS	_	plastic surface mounted package; 6 leads	SOT666		

15 V low $V_{CE(sat)}$ NPN double transistor

PBSS2515VS

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT		
Per transis	Per transistor unless otherwise specified						
V _{CBO}	collector-base voltage	open emitter	_	15	V		
V _{CEO}	collector-emitter voltage	open base	_	15	V		
V _{EBO}	emitter-base voltage	open collector	-	6	V		
Ic	collector current (DC)		_	500	mA		
I _{CM}	peak collector current		_	1	Α		
I _{BM}	peak base current		-	100	mA		
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	200	mW		
T _{stg}	storage temperature		-65	+150	°C		
Tj	junction temperature		_	150	°C		
T _{amb}	operating ambient temperature		-65	+150	°C		
Per device	•						
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	300	mW		

Note

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	notes 1 and 2	416	K/W

Notes

- 1. Transistor mounted on an FR4 printed-circuit board.
- 2. The only recommended soldering method is reflow soldering.

^{1.} Transistor mounted on an FR4 printed-circuit board.

15 V low $V_{CE(sat)}$ NPN double transistor

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CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Per transis	Per transistor unless otherwise specified						
I _{CBO}	collector-base cut-off current	V _{CB} = 15 V; I _E = 0 A	_	_	100	nA	
		V _{CB} = 15 V; I _E = 0 A; T _j = 150 °C	-	-	50	μΑ	
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A	-	-	100	nA	
h _{FE}	DC current gain	V _{CE} = 2 V; I _C = 10 mA	200	-	_		
		V _{CE} = 2 V; I _C = 100 mA; note 1	150	_	_		
		V _{CE} = 2 V; I _C = 500 mA; note 1	90	-	_		
V _{CEsat}	collector-emitter saturation	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	-	25	mV	
	voltage	I _C = 200 mA; I _B = 10 mA	-	-	150	mV	
		$I_C = 500 \text{ mA}$; $I_B = 50 \text{ mA}$; note 1	_	_	250	mV	
R _{CEsat}	equivalent on-resistance	$I_C = 500 \text{ mA}$; $I_B = 50 \text{ mA}$; note 1	-	300	<500	mΩ	
V _{BEsat}	base-emitter saturation voltage	$I_C = 500 \text{ mA}$; $I_B = 50 \text{ mA}$; note 1	-	-	1.1	V	
V_{BE}	base-emitter turn-on voltage	V _{CE} = 2 V; I _C = 100 mA; note 1	_	_	0.9	V	
f _T	transition frequency	$I_C = 100 \text{ mA}; V_{CE} = 5 \text{ V}; f = 100 \text{ MHz}$	250	420	_	MHz	
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = I_e = 0 \text{ A}; f = 1 \text{ MHz}$	_	4.4	6	pF	

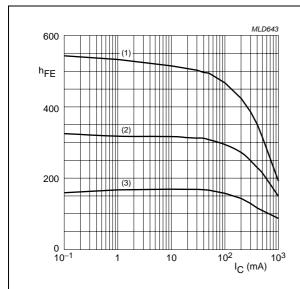
Note

1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

2004 Dec 23

15 V low $V_{CE(sat)}$ NPN double transistor

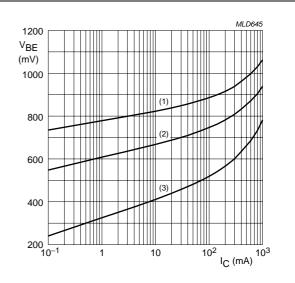
PBSS2515VS



V_{CE} = 2 V.

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

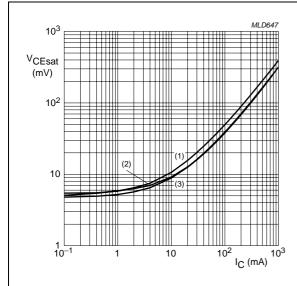
Fig.2 DC current gain as a function of collector current; typical values.



 $V_{CE} = 2 V.$

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

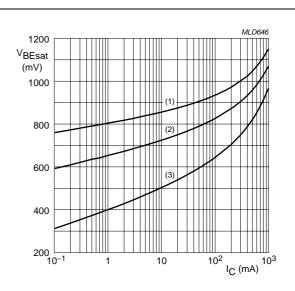
Fig.3 Base-emitter voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 20.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



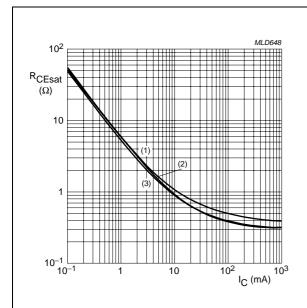
 $I_{\rm C}/I_{\rm B} = 20.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.5 Base-emitter saturation voltage as a function of collector current; typical values.

15 V low $V_{\text{CE(sat)}}$ NPN double transistor

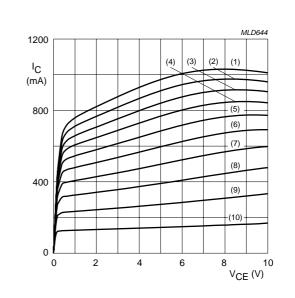
PBSS2515VS



 $I_{\rm C}/I_{\rm B}=20.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55$ °C.

Fig.6 Equivalent on-resistance as a function of collector current; typical values.



T_{amb} = 25 °C.

- (1) $I_B = 4.6 \text{ mA}.$
- (6) $I_B = 2.3 \text{ mA}.$
- (2) $I_B = 4.14 \text{ mA}.$
- (7) $I_B = 1.84 \text{ mA}.$
- (3) $I_B = 3.68 \text{ mA}.$
- (8) $I_B = 1.38 \text{ mA}.$
- (4) $I_B = 3.22 \text{ mA}.$
- (9) $I_B = 0.92 \text{ mA}.$
- (5) $I_B = 2.76 \text{ mA}.$
- (10) $I_B = 0.46$ mA.

Fig.7 Collector current as a function of collector-emitter voltage; typical values.

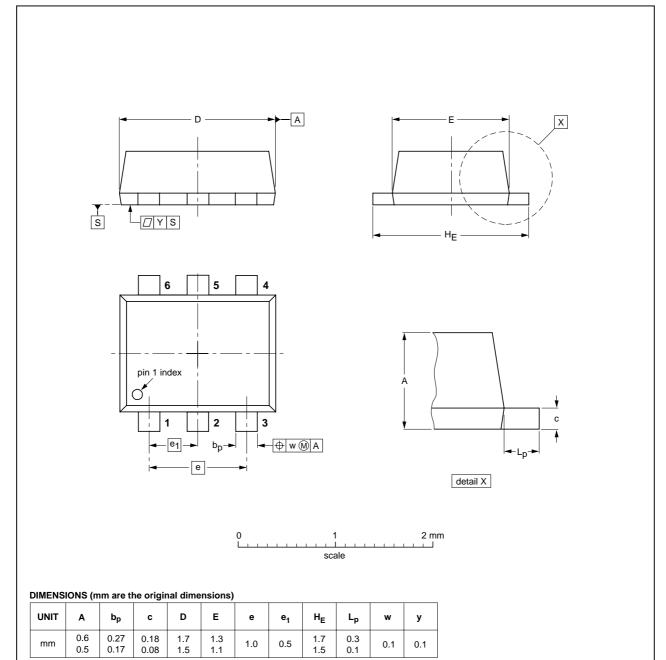
15 V low $V_{\text{CE(sat)}}$ NPN double transistor

PBSS2515VS

PACKAGE OUTLINE

Plastic surface-mounted package; 6 leads

SOT666



OUTLINE	INE REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT666						-04-11-08- 06-03-16

15 V low V_{CE(sat)} NPN double transistor

PBSS2515VS

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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